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Micro-LED is more robust, longer-lived and compatible with conventional fabrication processes. Recently the micro-LED based display has attracted considerable attention because of various applications such as smart watches, smartphone and large size display. However, the display which has been demonstrated was passive matrix (PM) type, which sequentially addresses each pixel in a row-column scheme with a high rastering frequency, requires high power consumption. These limitations restrict the application range of PM displays.

To address the issue, we integrated a stretchable, active matrix (AM)-type inorganic LED display driven by thin film transistors (TFTs) fabricated from single crystal Si, which would achieve large-size displays with rapid response time and low power consumption. The micro-LEDs and Si-TFTs were moved from source wafers to a rubber substrate by triple successive transfers with a soft roller stamp and high overlay alignment. To improve the electro-mechanical stretchability, the LEDs and TFTs were interconnected with each other using serpentine-shaped metallic thin films.<sup>[1]</sup>

In addition, we present the synthesis of high quality and uniform, wafer scale MoS<sub>2</sub> and modified switching device architecture for efficiently exploiting the high-k dielectric Al<sub>2</sub>O<sub>3</sub> layer, which, when integrated in an active matrix can drive the ultrathin OLED display even in dynamic folding states.<sup>[2]</sup>

## References

[1] M. Choi et al., *Advanced Functional Materials* 27, 1606005 (2017)

[2] M. Choi et al., *Science Advances* 4:eaas8721 (2018)